

# **PSMN011-80YS**

# N-channel LFPAK 80 V 11 m $\Omega$ standard level MOSFET

Rev. 02 — 28 October 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	67	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	-	18	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}};$	-	8.6	11	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$	-	11	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	45	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 67 A; $V_{sup} \le$ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	-	121	mJ

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN011-80YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	47	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	67	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$ ; see Figure 3	-	266	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	117	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	67	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	266	Α
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 67 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	121	mJ

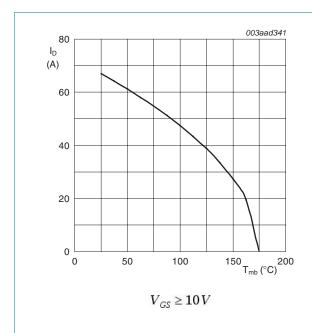


Fig 1. Continuous drain current as a function of mounting base temperature

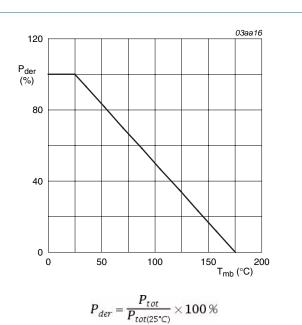
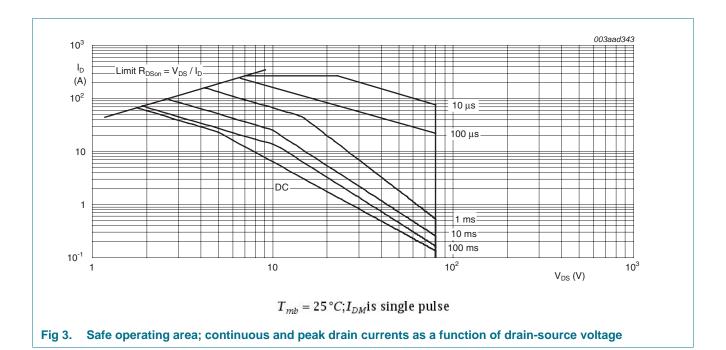


Fig 2. Normalized total power dissipation as a function of mounting base temperature



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.3	K/W

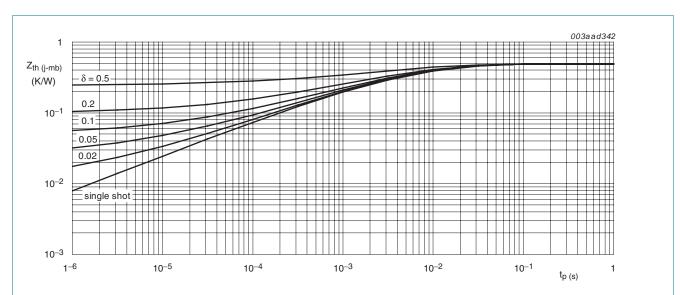


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
$V_{(BR)DSS}$ drain-source breakdown $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 100 \mu A; V_{GS} = 10$		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see <u>Figure 10</u>	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub> gate leakage cui	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	19	26	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	-	-	18	mΩ	
	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	8.6	11	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	38	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	45	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	13	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14	-	8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	5	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.9	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2800	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	270	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	146	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 1.6 \Omega; V_{GS} = 10 \text{ V};$	-	23	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	40	-	ns
t <sub>f</sub>	fall time		-	12	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 40 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ;	-	54	-	ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	-	98	-	nC

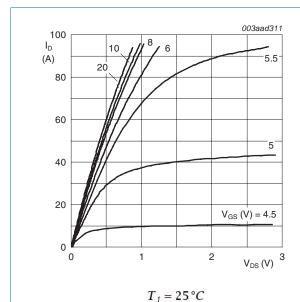


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

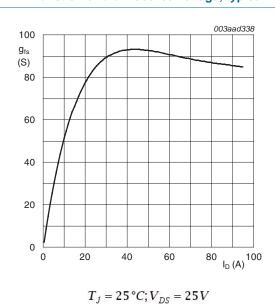
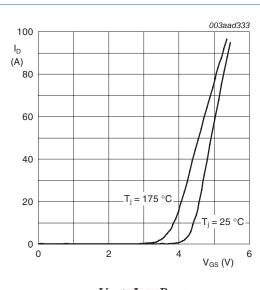
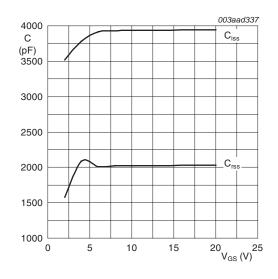


Fig 7. Forward transconductance as a function of drain current; typical values



 $V_{DS} > I_D imes R_{DSon}$ 

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $V_{DS} = 0V; f = 1MHz$ 

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

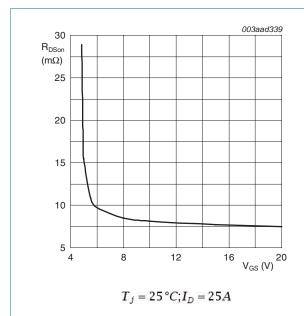
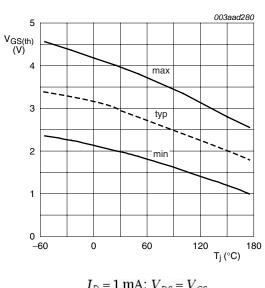


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

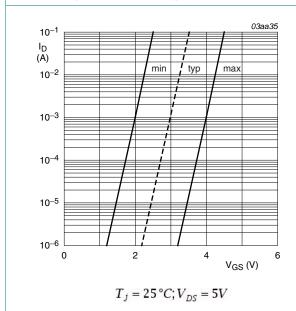


Fig 11. Sub-threshold drain current as a function of gate-source voltage

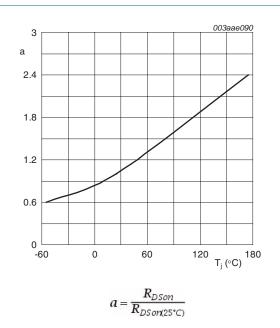


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

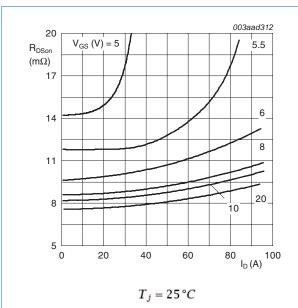
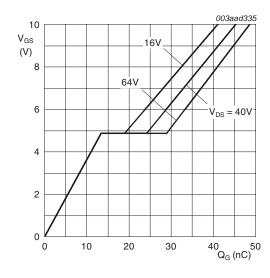
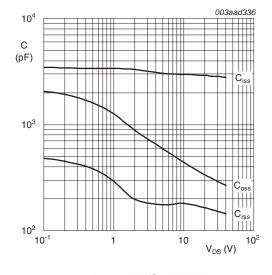


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j=25\,^{\circ}C; I_D=25A$ 

 $V_{GS} = 0V; f = 1MHz$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

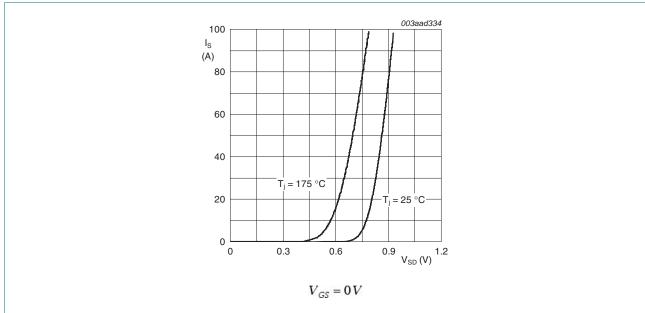
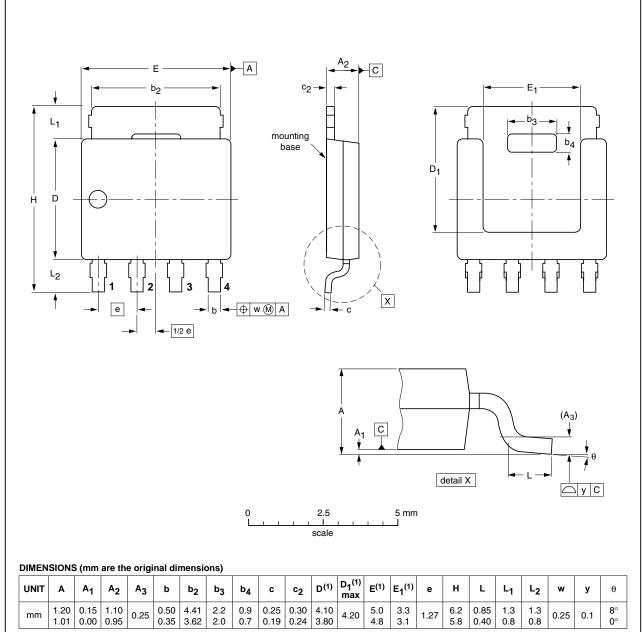


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline

# Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 



#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235			$ \  \   \bigoplus   \big($	<del>04-10-13</del> 06-03-16

Fig 18. Package outline SOT669 (LFPAK)

PSMN011-80YS

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# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-80YS v.2	20101028	Product data sheet	-	PSMN011-80YS v.1
Modifications:				
	<ul> <li>Various change</li> </ul>	es to content.		
PSMN011-80YS v.1	20100226	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PSMN011-80YS**

### **Nexperia**

N-channel LFPAK 80 V 11 mΩ standard level MOSFET

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